

Electronic band gaps and transport in aperiodic graphene superlattices of Thue-Morse sequence

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We have studied the electronic properties in aperiodic graphene superlattices of Thue-Morse sequence. Although the structure is aperiodic, an unusual Dirac point (DP) does exist and its location is exactly at the position of the zero-averaged wave number (zero- $\bar{k}$). Furthermore, the zero- $\bar{k}$ gap associated with the DP is robust against the lattice constants and the incident angles, and multi-DPs can appear under the suitable conditions. A resultant controllability of electron transport in Thue-Morse sequence is predicted, which may facilitate the development of many graphene-based electronics.

Graphene has attracted enormous attention of experimentalists and theorists [1–8] since its discovery. The interest is driven by its potential technological applications and unconventional low energy behavior. This is mainly because graphene has a unique band structure with the conductance and valance bands touching at Dirac point (DP). Recently, scientists anticipate that graphene-based electronics may supplement silicon-based technology, which is nearing its limits [9]. For superlattices are vastly successful to control the electronic transport [10], to facilitate the application of graphene-based electronics, the graphene superlattices (GSLs) with electrostatic potential or magnetic barrier have also received broad focuses of theoretical and experimental investigations [11–20]. In such GSLs, the new DP appears in the band structures [15, 16] and it's exactly located at the energy corresponding to zero-averaged wave number (zero- $\bar{k}$) [17]. Contrary to Bragg gaps, the zero- $\bar{k}$ gap associated with the new DP is insensitive to both the lattice constant and the structural disorder, resulting in better controllability of electronic transport in GSLs. Most recently, Zhao and Chen predicted a controllable electron transport in a Fibonacci quasi-periodic GSL [18].

In this letter, we investigate the electronic band gaps and transport in the GSLs of Thue-Morse (TM) sequence. Although such a TM sequence is aperiodic and it is more “disordered” than the Fibonacci sequence [21, 22], we find that zero- $\bar{k}$ gap and DP do exist in such a GSL TM sequence, which results in robust electronic transport properties.

For a TM sequence, it can be generated in various ways. For an n -th TM sequence, $S(n)$, it contains only 2 elements A and B , and follows the inflation rule: $A \rightarrow AB$, $B \rightarrow BA$ from generation to generation with $S(1) = AB$ (for example, see Ref. [23]). Let $S_{1/2}^L(n)$ and $S_{1/2}^R(n)$ denote the left and right half parts of an n -th order TM sequence respectively, then iteration relation

for any $(n + 1)$ -th TM sequence is written as

$$S(n + 1) = S(n) S_{1/2}^R(n) S_{1/2}^L(n). \quad (1)$$

Naturally, $S(2) = ABBA$, $S(3) = ABBABAAB$, and so on. In our cases, A (B) denotes barrier V_A (V_B) with its width w_A (w_B). It is readily to know that the number of A , N_A , equals to that of B , N_B , in any $S(n)$, i.e., $N_A = N_B = 2^{n-1}$.

Meanwhile the charge carriers near the $\mathbf{K}$ point in graphene (near the Fermi level) are described by its Hamilton: $\hat{H} = v_F \hat{\sigma} \cdot \hat{\mathbf{p}} + V(x) \hat{I}$, where $V(x)$ is a barrier or well, $v_F \approx 10^6$ m/s is the Fermi velocity, $\hat{\sigma} = (\hat{\sigma}_x, \hat{\sigma}_y)$ are Pauli matrices, and $\hat{I}$ is a 2×2 unit matrix. The solution of $\hat{H}$ acting on the electronic pseudospin wavefunctions leads to a transfer matrix [17]

$$M_j(\Delta x, E, k_y) = \begin{pmatrix} \frac{\cos(q_j \Delta x - \theta_j)}{\cos \theta_j} & i \frac{\sin(q_j \Delta x)}{\cos \theta_j} \\ i \frac{\sin(q_j \Delta x)}{\cos \theta_j} & \frac{\cos(q_j \Delta x + \theta_j)}{\cos \theta_j} \end{pmatrix}, \quad (2)$$

which connects the wave functions at two positions x and $x + \Delta x$ inside the j th potential with $\theta_j = \arcsin(k_y/k_j)$, here k_y is the y component of the wave number k_j , and $q_j = \text{sign}(k_j) \sqrt{k_j^2 - k_y^2}$ for $k_y^2 < k_j^2$, otherwise $q_j = i \sqrt{k_y^2 - k_j^2}$ for $k_y^2 > k_j^2$. The electronic transmission coefficient $t(E, k_y)$ in such devices can be obtained by [17]

$$t(E, k_y) = \frac{2 \cos \theta_0}{(x_{22} e^{-i\theta_0} + x_{11} e^{i\theta_e}) - x_{12} e^{i(\theta_e - \theta_0)} - x_{21}}, \quad (3)$$

where θ_0 (θ_e) is the incident (exit) angle, and x_{ij} ($i, j = 1, 2$) is the element of $\mathbf{X}[S(n)] = \prod_{j=1}^N M_j(w_j, E, k_y)$, which is the entire transfer matrix of a GSL TM sequence. If we let $x_n = \text{Tr}\{\mathbf{X}[S(n)]\}$, it is readily to derive the iteration

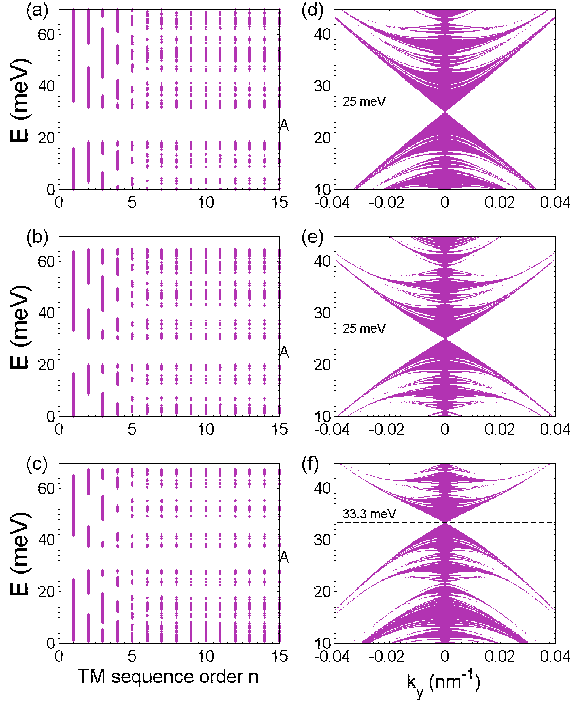


FIG. 1: (Color online) Trace-maps for GSL TM sequences of variable order n under (a) $w_{A,B} = 20$ nm, (b) $w_{A,B} = 25$ nm and (c) $w_A = 2w_B = 40$ nm with $V_A = 50$ meV, $V_B = 0$ and the wave number $k_y = 0.015$ nm $^{-1}$. (d), (e) and (f) are band structures for $n = 8$ corresponding to (a), (b) and (c) respectively as k_y varies. The horizontal dashed black line denotes the new Dirac point's location, and the white areas are band gaps and the solid areas are passing bands.

relation for the trace map of the n -th GSL TM sequence as follows [23–25]:

$$x_n = x_{n-2}^2 (x_{n-1} - 2) + 2. \quad (4)$$

Treating an n -th TM sequence as a unit cell, from Bloch's theorem, we have $\cos(\beta_x \Lambda_n) = x_n/2$, where $\Lambda_n = N_A w_A + N_B w_B$. From Eq.(4), we can calculate the change of the trace map as a function of the order n .

In Fig. 1 (a) and (b), we plot the trace maps for two kinds of GSL TM sequences dependent on the order n , at the incident angle $\theta_0 = 10^\circ$. We take $w_{A,B} = 20$ nm in Fig. 1(a), and $w_{A,B} = 25$ nm in Fig. 1(b). We find that the passing bands are split into more and more sub-bands as n increases; when $n \geq 6$, the band structures almost become the discontinuous bands. However, we note that the center position of the Gap A in Figs. 1(a) and 1(b) are the same, and the positions of other gaps are shifted with the change of the lattice constant. Corresponding to Fig. 1(a) and 1(b), the electronic band structures for a TM sequence of $n = 8$ have been shown in Fig. 1(d) and 1(e), respectively. It is seen that a new DP appears

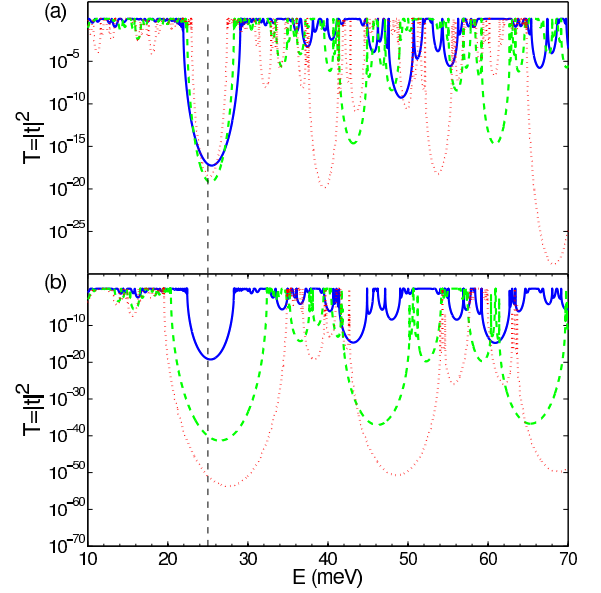


FIG. 2: (Color online) Transmission spectrum for an 8-th GSL TM sequence (256 layers) where $V_A = 50$ meV, $V_B = 0$, (a) $w_A = 15$ nm (solid blue line), 20 nm (dashed green), 25 nm (dotted red) with a fixed ratio $w_A/w_B = 1$ and an incident angle $\theta_0 = 10^\circ$, and (b) $\theta_0 = 10^\circ$ (solid blue line), 20° (dashed green), and 25° (dotted red) with fixed lattice constants $w_{A,B} = 20$ nm.

inside the Gap and this new DP actually locates at

$$\bar{k} = \sum_{j=1}^N k_j w_j / \sum_{j=1}^N w_j = 0. \quad (5)$$

This condition is valid for periodic and aperiodic graphene superlattices [16–18]. Since $N_A = N_B$ in our cases, it is easily to obtain the energy for $\bar{k} = 0$ as follows:

$$E = \frac{V_A + V_B \cdot w_B/w_A}{1 + w_B/w_A}. \quad (6)$$

In the cases of Fig. 1(a,b,d,e), it is given by $E = 25$ meV as $w_A = w_B$.

Since the center of the Gap A in Fig. 1 is located at zero- $\bar{k}$, which is denoted by a dashed black line in Fig. 1 (a) and (b), we may call it as the zero- $\bar{k}$ gap. According to Eq.(6), the position of the zero- $\bar{k}$ gap for the GSL TM sequences is not shifted with the lattice constant itself, but is shifted with the change of the ratio of w_A/w_B . As shown in Fig. 1 (c) and (f), the position of the zero- $\bar{k}$ gap and the DP move to $E \approx 33.33$ meV for $w_A/w_B = 2$.

Fig.2 (a) shows the effect of the lattice constants' variation with a fixed ratio of $w_A/w_B = 1$. Based on Fig.2 (a), it is obvious that the zero- $\bar{k}$ gap is insensitive to the lattice constants themselves. However, the positions of other gaps with higher energy are highly dependent on the lattice parameters. From Fig. 2(b), one can also find that the position of zero- $\bar{k}$ gap is weakly dependent

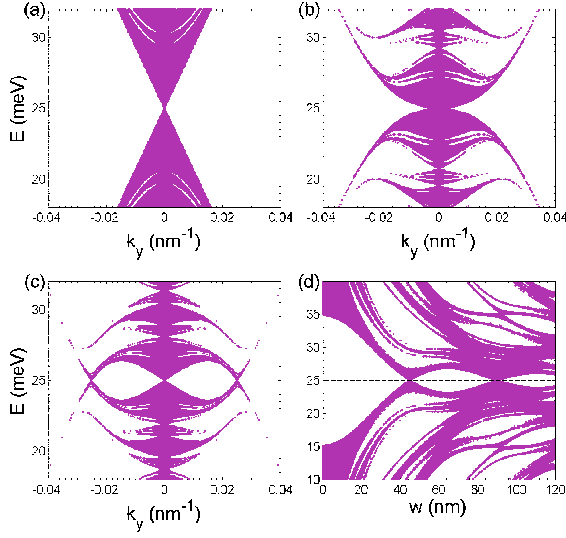


FIG. 3: (Color online) Electronic band structures for (a) $w_{A,B} = 20$ nm, (b) $w_{A,B} = 40$ nm and (c) $w_{A,B} = 55$ nm; (d) band gaps depending on the lattice constant w with fixed $k_y = 0.015 \text{ nm}^{-1}$ and $w_A = w_B = w$. Other parameters are the same as those in Fig.1.

on the incident angle θ_0 while other Bragg gaps change sensitively with θ_0 .

Furthermore, one has known that the multi-Dirac-points could appear in the GSLs with periodic potential structures[16, 17]. Here we point out that the extra Dirac points, located at $k_y \neq 0$, could also emerge in the GSL TM sequence as the lattice constant increases. See Figs.3(a) and (b), the slope of the band edges near the DP gradually turns smaller as w_A (w_B) increases from 20 nm to 40 nm. When w_A (w_B) is larger than 40 nm, as that shown in Fig. 3 (c), the additional Dirac points appear. From Figs.3(a) to (c), we may also find the appearance of additional Dirac points associating with the variation of the zero- $\bar{k}$ gap. In Fig.3 (d), we show the energy band gaps as a function of the lattice constants in the case of $w_A = w_B$. In the process of the appearance of the additional Dirac points, the zero- $\bar{k}$ gap opens and closes oscillationally while the other gaps are shifted greatly.

Finally, we calculate the total conductance G [26] and the Fano factor F [27] in GSL TM sequences, which are given by $G = G_0 \int_0^{\pi/2} T \cos \theta_0 d\theta_0$ and $F = \int_{-\pi/2}^{\pi/2} T (1 - T) \cos \theta_0 d\theta_0 / \int_{-\pi/2}^{\pi/2} T \cos \theta_0 d\theta_0$, where $T = |t|^2$ and $G_0 = 2e^2 m v_F L_y / \hbar^2$, with L_y denoting the width of the graphene stripe in the y direction. We present the total conductance and the Fano factor as a function of Fermi energy with different lattice constants in Fig.4. What we should notice is that the angular-averaged conductance G 's curve reaches its minimum at the DP and forms a linear cone around the

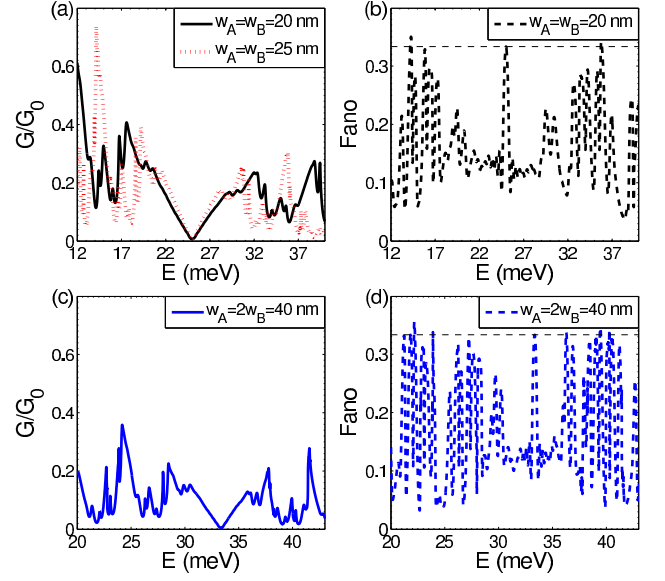


FIG. 4: (Color online) Conductance ((a) and (c)) and Fano factor ((b) and (d)) vs Fermi energy in an 8-th GSL TM sequence. Other parameters are the same as those in Fig.1.

DP, and F at the DP's location reaches the value of $1/3$ approximately[20, 27]. Moreover, the conductance and the Fano factor shift with the ratio of w_A/w_B since the DP's location relies on this ratio. Therefore, this suggests that the conductance of GSL TM sequence could be modulated by the ratio of the lattice constants.

In summary, we have studied the electronic transport properties in the GSLs of Thue-Morse aperiodic sequence. It is found that an unusual DP does exist and its location is exactly at the energy corresponding to the zero- $\bar{k}$ in such aperiodic structures. The zero- $\bar{k}$ gap associated with the DP is robust against the lattice constants and the incident angles, and the extra-DPs can appear under the suitable conditions. A resultant controllable electron transport is predicted, and our results should facilitate the development of graphene-based electronics.

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